

What is claimed is:

1 1. An integrated circuit structure comprising:
 2 a plastic substrate;
 3 a layer of silicon dioxide or silicon nitride having a thickness such that little
 4 or no differential strain between the substrate and said layer occurs in the normal
 5 operating temperature range of said integrated circuit;
 6 an antenna conductor which is bonded onto, integrated onto or printed onto
 7 said substrate and having two conductive pads or other conductive terminal areas
 8 where electrical connection to said antenna may be made;
 9 an RFID tag or smart card transceiver integrated circuit integrated on said
 10 substrate so as to have RF input/output terminals which are electrically coupled to
 11 said terminal areas of said antenna.

1 2. An integrated circuit structure comprising:
 2 a plastic substrate;
 3 a layer of silicon dioxide or silicon nitride having a thickness such that little
 4 or no differential strain between the substrate and said layer occurs in the normal
 5 operating temperature range of said integrated circuit;
 6 an RFID tag or smart card transceiver integrated circuit integrated on said
 7 substrate on top of said layer of silicon dioxide or silicon nitride so as to have RF
 8 input/output terminals, and having a layer of insulating material formed over said
 9 integrated circuit;
 10 an antenna conductor which is bonded onto, integrated onto or printed onto
 11 said insulating layer covering said integrated circuit so as to make electrical
 12 connection with said RF input/output terminals.

1 3. An integrated circuit structure comprising:
 2 a first plastic or glass or plastic laminated to glass substrate;

3 a layer of silicon dioxide or silicon nitride having a thickness such that little
 4 or no differential strain between the substrate and said layer occurs in the normal
 5 operating temperature range of said integrated circuit;

6 an antenna conductor which is bonded onto, integrated onto or printed onto
 7 said substrate and having two conductive pads or other conductive terminal areas
 8 where electrical connection to said antenna may be made;

9 an RFID tag or smart card transceiver integrated circuit integrated as one of a
 10 very large number of said integrated circuits on a large second plastic or glass
 11 substrate using flat panel display manufacturing equipment, said integrated circuit
 12 being cut from said second plastic or glass substrate and bonded or otherwise
 13 attached to said first plastic substrate and having RF input/output terminals; and

14 wires connected in any way between said RF input/output terminals of said
 15 integrated circuit and said terminal areas of said antenna.

1 4. A process of making a large number of integrated circuits on a large plastic or
 2 glass or plastic laminated to glass substrate comprising:

3 selecting a plastic or glass or plastic laminated to glass substrate having a
 4 large size which is compatible with the substrate size capacity of flat panel display
 5 manufacturing machines to be used to do the subsequent deposition, photolithography,
 6 etching and laser crystallization and annealing steps necessary to form an integrated
 7 circuit thereon;

8 depositing a layer of insulating material which has a thickness and Young's
 9 Modulus which are selected in light of the thickness and Young's Modulus of said
 10 substrate so as to reduce differential strain at anticipated operating temperatures so
 11 as to eliminate or reduce reliability problems using processing steps performed at
 12 temperatures or in a manner which will not exceed the glass transition temperature
 13 of said substrate and using chemicals which will not chemically attack or otherwise
 14 damage said substrate;

15 forming an antenna with one or more terminals on said layer of insulating
 16 material using processing steps performed at temperatures or in a manner which

will not exceed the glass transition temperature of said substrate and using chemicals which will not chemically attack or otherwise damage said substrate; using flat panel display manufacturing machines to deposit a layer of insulating material over said antenna and to do the insulation, metal and semiconductor deposition steps, and the photolithography, etching and pulsed laser crystallization and annealing steps necessary to form an integrated circuit of a desired functionality directly on said substrate so as to RF input/output terminals in electrical contact with said one or more antenna terminals, all said processing steps performed at temperatures or in a manner which will not exceed the glass transition temperature of said substrate and using chemicals which will not chemically attack or otherwise damage said substrate.

5. A process of making a large number of integrated circuits on a large substrate comprising:

selecting a first plastic or glass or plastic laminated to glass substrate having a large size which is compatible with the substrate size capacity of flat panel display manufacturing machines to be used to do the subsequent deposition, photolithography, etching steps needed to form an antenna or compatible with the substrate size capacity that can be processed by a silk screen printer to print an antenna;

depositing a layer of insulating material which has a thickness and Young's Modulus which are selected in light of the thickness and Young's Modulus of said substrate so as to reduce differential strain at anticipated operating temperatures so as to eliminate or reduce reliability problems using a process which will not melt, warp, deform, chemically attack or otherwise damage said first substrate;

using a flat panel display manufacturing machine or silk screen printer to form a plurality of antennas at a plurality of locations on said first substrate with one or more terminals on said layer of insulating material using deposition, photolithography, etching or printing processes which will not melt, warp, deform, chemically attack or otherwise damage said first substrate;

dicing said first substrate up into many individual substrates, each with its own antenna formed thereon;

20 selecting a second plastic or glass or plastic laminated to glass substrate
21 having a large size which is compatible with the substrate size capacity of flat panel
22 display manufacturing machines to be used to do subsequent deposition,
23 photolithography, etching and laser crystallization and annealing steps necessary to
24 form a thin film integrated circuit;

25 using flat panel display manufacturing machines to do the insulation, metal
26 and semiconductor deposition steps, and the photolithography, etching and pulsed
27 laser crystallization and annealing steps necessary to form an integrated circuit of a
28 desired functionality on said second substrate so as to RF input/output terminals, all
29 said processing steps performed at temperatures or in a manner which will not
30 exceed the glass transition temperature of said second substrate and using chemicals
31 which will not chemically attack or otherwise damage said second substrate;

32 dicing said second substrate up into many integrated circuits and bonding or
33 otherwise attaching each functional integrated circuit to one of said individual plastic
34 substrates cut from said first substrate; and

35 wire bonding wires to connect said RF input/output terminals of said
36 integrated circuit to said one or more terminals of said antenna on said individual
37 first substrate.

1 6. A process of making a large number of integrated EEPROM cells on a large
2 substrate comprising:

3 selecting a plastic or plastic laminated to glass substrate having a large size
4 which is compatible with the substrate size capacity of flat panel display
5 manufacturing machines to be used to do the subsequent deposition, photolithography,
6 etching and laser crystallization and annealing steps necessary to form said EEPROM
7 cells thereon;

8 depositing a layer of insulating material which has a thickness and Young's
9 Modulus which are selected in light of the thickness and Young's Modulus of said
10 substrate so as to reduce differential strain at anticipated operating temperatures so
11 as to eliminate or reduce reliability problems using processing steps performed at
12 temperatures or in a manner which will not exceed the glass transition temperature

of said plastic substrate and using chemicals which will not chemically attack or otherwise damage said plastic substrate;

using flat panel display manufacturing machines to do the insulation, metal and semiconductor deposition steps, and the photolithography, etching and pulsed laser crystallization and annealing steps necessary to form a plurality of EEPROM memory cells directly on said plastic substrate, all said processing steps performed at temperatures or in a manner which will not exceed the glass transition temperature of said plastic substrate and using chemicals which will not chemically attack or otherwise damage said plastic substrate.

7. A process for manufacturing an integrated circuit including MOS transistors and EEPROM cells on a substrate comprising:

selecting a plastic or plastic laminated to glass substrate having a large size which is compatible with the substrate size capacity of flat panel display manufacturing machines to be used to do the subsequent deposition, photolithography, etching and laser crystallization and annealing steps necessary to form said integrated circuit thereon;

using flat panel display manufacturing machines to perform the following steps:

depositing a layer of insulating material which has a thickness and Young's Modulus which are selected in light of the thickness and Young's Modulus of said substrate so as to reduce differential strain at anticipated operating temperatures so as to eliminate or reduce reliability problems using processing steps performed at temperatures or in a manner which will not exceed the glass transition temperature of said substrate and using chemicals which will not chemically attack or otherwise damage said substrate;

depositing a layer of amorphous silicon which is between 10 and 5000 nanometers thick by sputtering or by plasma enhanced chemical vapor deposition hereafter referred to as PECVD using processing steps performed at temperatures or in a manner which will not exceed the glass transition

23 temperature of said substrate and using chemicals and/or gases which will
24 not chemically attack or otherwise damage said substrate;

25 if higher mobilities or higher ON currents or lower threshold
26 voltages for MOS transistors are needed for the transistors to be formed in
27 said silicon layer than can be achieved in amorphous silicon, crystallizing said
28 silicon layer to polycrystalline or microcrystalline form by pulse annealing
29 the silicon layer with an excimer laser having a 308 nm wavelength using
30 pulse durations of 30 nanoseconds or less full width at half maximum and
31 energy density between 30-600 mJ/cm² per pulse using one or more pulses;

32 masking off areas of said integrated circuit where EEPROM cells, if
33 any, are to be formed, and depositing a layer of gate insulator by PECVD at
34 a temperature below the glass transition temperature of said substrate, said
35 layer having a thickness suitable for thin film metal-oxide-semiconductor
36 transistor device operation, typically between 20-500 nanometers thick;

37 masking off areas where MOS transistors are being formed to expose
38 areas where EEPROM memory cells are to be formed and depositing one or
39 more layers of gate insulator to form an insulation layer that is to lie below
40 the floating gate, the thickness and materials selected for said one or more
41 layers of gate insulator being such as to achieve Fowler-Noordheim
42 tunnelling to the floating gate from a channel region at whatever
43 programming voltage can be achieved on said integrated circuit, said
44 deposition being accomplished by PECVD at a temperature below the glass
45 transition temperature of said substrate;

46 depositing a layer of gate conductor, typically metal or silicides by
47 physical vapor deposition (hereafter PVD), chemical vapor deposition
48 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
49 process to form a control gate at the MOS transistor locations and a floating
50 gate at the EEPROM cell locations, said deposition being accomplished at a
51 temperature below the glass transition temperature of said substrate;

52 masking off locations where MOS transistors are being formed to leave
53 exposed only locations where EEPROM cells are being formed, and depositing a

54 layer of intergate insulator from which will be formed the insulation layer
55 between the floating gate and the control gate of each EEPROM cell, said
56 deposition being accomplished by PECVD or some other process which will
57 form an insulator of high enough quality to prevent charge leakage from said
58 floating gate and at a temperature below the glass transition temperature of
59 said substrate;

60 masking off locations where MOS transistors are being formed to leave
61 exposed only locations where EEPROM cells are being formed, and depositing a
62 layer of metal or silicide from which the control gate of all EEPROM cells is
63 to be formed, said deposition being by PVD, CVD, PECVD, evaporation or
64 sputtering or some other suitable process and accomplished at a temperature
65 below the glass transition temperature of said substrate;

66 performing the necessary photolithographic etching to define the gate
67 islands at both said MOS transistor and EEPROM cell locations, said
68 photolithographic etching being accomplished at temperatures below the glass
69 transition temperature of said substrate and using chemicals and/or gases
70 which will not attack or otherwise damage said substrate;

71 doping the source and drain regions of all said MOS transistors and
72 EEPROM cells using the Gas Immersion Laser Doping process or any other
73 suitable doping process which can dope said source and drain regions to
74 suitable conductivity and which crystallizes said amorphous silicon by pulsed
75 laser annealing and which can be accomplished at a temperature below the
76 glass transition temperature of said substrate and using chemicals and/or
77 gases which will not attack or otherwise damage said substrate;

78 photolithographically etching to define the lateral extents of each thin
79 film transistor island at each MOS transistor and EEPROM cell, said
80 photolithographic etching being accomplished at temperatures below the glass
81 transition temperature of said substrate and using chemicals and/or gases
82 which will not attack or otherwise damage said substrate;

83 depositing an insulation layer over all MOS transistors and EEPROM
84 cells and etching vias therethrough for source, drain and control gate contacts

85 at all MOS transistor and EEPROM cell locations, said deposition being
86 accomplished at temperatures below the glass transition temperature of said
87 substrate and using chemicals and/or gases which will not attack or
88 otherwise damage said substrate;

89 depositing a layer of contact metallization conductor to fill said via
90 holes and cover each MOS transistors and EEPROM cell location and the spaces
91 therebetween, and photolithographically etching the conductor layer to form a
92 contact metallization to connect all the MOS transistors and EEPROM cells
93 together to form the desired integrated circuit functionality.

1 8. The process of claim 7 wherein said integrated circuit is an RFID tag transceiver,
2 a smart card or a toy controller and further comprising the steps of etching said contact
3 metallization conductor layer appropriately to form RF input/output terminals, and further
4 comprising the step of printing or photolithographically forming a conductive antenna on
5 said substrate so as to make electrical contact with said RF input/output terminals.

1 9. A process for manufacturing an integrated circuit including MOS transistors and
2 ROM cells on a substrate comprising:

3 selecting a plastic or plastic laminated to glass substrate having a large size
4 which is compatible with the substrate size capacity of flat panel display
5 manufacturing machines to be used to do the subsequent deposition, photolithography,
6 etching and laser crystallization and annealing steps necessary to form said
7 integrated circuit thereon;

8 using flat panel display manufacturing machines to perform the following
9 steps:

10 depositing a layer of insulating material which has a thickness and
11 Young's Modulus which are selected in light of the thickness and Young's
12 Modulus of said substrate so as to reduce differential strain at anticipated
13 operating temperatures so as to eliminate or reduce reliability problems
14 using processing steps performed at temperatures or in a manner which will
15 not exceed the glass transition temperature of said substrate and using

chemicals which will not chemically attack or otherwise damage said substrate;

depositing a layer of amorphous silicon which is between 10 and 500 nanometers thick by sputtering or by plasma enhanced chemical vapor deposition hereafter referred to as PECVD using processing steps performed at temperatures or in a manner which will not exceed the glass transition temperature of said substrate and using chemicals and/or gases which will not chemically attack or otherwise damage said substrate;

if higher mobilities or higher ON currents or lower threshold voltages for MOS transistors are needed for the transistors to be formed in said silicon layer than can be achieved in amorphous silicon, crystallizing said silicon layer to polycrystalline or microcrystalline form by pulse annealing the silicon layer with an excimer laser having a 308 nm wavelength using pulse durations of 30 nanoseconds or less full width at half maximum and energy density between 30-600 mJ/cm² per pulse using one or more pulses;

masking off areas of said integrated circuit where ROM cells, if any, are to be formed, and depositing a layer of gate insulator by PECVD at a temperature below the glass transition temperature of said substrate, said layer having a thickness suitable for thin film metal-oxide-semiconductor transistor device operation, typically between 20-500 nanometers thick;

masking off areas where MOS transistors are being formed to expose areas where ROM memory cells are to be formed and depositing one or more layers of gate insulator to form an insulation layer that is to lie below the floating gate, the thickness and materials selected for said one or more layers of gate insulator being such as to achieve Fowler-Noordheim tunnelling to the floating gate from a channel region at whatever programming voltage can be achieved on said integrated circuit, said deposition being accomplished by PECVD at a temperature below the glass transition temperature of said substrate;

depositing a layer of gate conductor, typically metal or silicides by physical vapor deposition (hereafter PVD), chemical vapor deposition

47 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
48 process to form a control gate at the MOS transistor locations and a floating
49 gate at the ROM cell locations, said deposition being accomplished at a
50 temperature below the glass transition temperature of said substrate;

51 masking off locations where MOS transistors are being formed to leave
52 exposed only locations where ROM cells are being formed, and depositing a
53 layer of intergate insulator from which will be formed the insulation layer
54 between the floating gate and the control gate of each ROM cell, said deposition
55 being accomplished by PECVD or some other process which will form an
56 insulator of high enough quality to prevent charge leakage from said floating
57 gate and at a temperature below the glass transition temperature of said
58 substrate;

59 masking off locations where MOS transistors are being formed to leave
60 exposed only locations where ROM cells are being formed, and depositing a
61 layer of metal or silicide from which the control gate of all ROM cells is to be
62 formed, said deposition being by PVD, CVD, PECVD, evaporation or sputtering
63 or some other suitable process and accomplished at a temperature below the
64 glass transition temperature of said substrate;

65 performing the necessary photolithographic etching to define the gate
66 islands at both said MOS transistor and ROM cell locations, said
67 photolithographic etching being accomplished at temperatures below the glass
68 transition temperature of said substrate and using chemicals and/or gases
69 which will not attack or otherwise damage said substrate;

70 doping the source and drain regions of all said MOS transistors and
71 ROM cells using the Gas Immersion Laser Doping process or any other
72 suitable doping process which can dope said source and drain regions to
73 suitable conductivity and which crystallizes said amorphous silicon by pulsed
74 laser annealing and which can be accomplished at a temperature below the
75 glass transition temperature of said substrate and using chemicals and/or
76 gases which will not attack or otherwise damage said substrate;

77 photolithographically etching to define the lateral extents of each thin
78 film transistor island at each MOS transistor and ROM cell, said
79 photolithographic etching being accomplished at temperatures below the glass
80 transition temperature of said substrate and using chemicals and/or gases
81 which will not attach or otherwise damage said substrate;

82 depositing an insulation layer over all MOS transistors and ROM cells
83 and etching vias therethrough for source, drain and control gate contacts at
84 all MOS transistor and ROM cell locations, said deposition being accomplished
85 at temperatures below the glass transition temperature of said substrate and
86 using chemicals and/or gases which will not attack or otherwise damage said
87 substrate;

88 depositing a layer of contact metallization conductor to fill said via
89 holes and cover each MOS transistors and ROM cell location and the spaces
90 therebetween, and photolithographically etching the conductor layer to form a
91 contact metallization to connect all the MOS transistors and ROM cells
92 together to form the desired integrated circuit functionality.

10. A process for manufacturing an integrated circuit with MOS and EEPROM cells
formed over an antenna on a substrate comprising:

3 selecting a plastic or plastic laminated to glass substrate having a large size
4 which is compatible with the substrate size capacity of flat panel display
5 manufacturing machines to be used to do the subsequent deposition, photolithography,
6 etching and laser crystallization and annealing steps necessary to form said
7 integrated circuit thereon;

8 using flat panel display manufacturing machines to perform the following
9 steps:

10 depositing a layer of insulating material which has a thickness and
11 Young's Modulus which are selected in light of the thickness and Young's
12 Modulus of said substrate so as to reduce differential strain at anticipated
13 operating temperatures so as to eliminate or reduce reliability problems
14 using processing steps performed at temperatures or in a manner which will

not exceed the glass transition temperature of said substrate and using chemicals which will not chemically attack or otherwise damage said substrate;

forming an antenna with one or more terminals on said layer of insulating material deposited in the previous step at a plurality of locations on said substrate by any prior art process such as silk screening or deposition and photolithographic etching accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases that will not attack or otherwise damage said substrate;

using flat panel display manufacturing machines to perform the following steps:

depositing a layer of pad contact conductor such as metal or silicides by physical vapor deposition (hereafter PVD), chemical vapor deposition (hereafter CVD), PECVD, evaporation or sputtering or some other suitable process and photolithographically etching to form lead line conductors from each antenna terminal to the locations where RF input/output terminals of each corresponding integrated circuit will be formed, said deposition being accomplished at a temperature below the glass transition temperature of said substrate;

depositing a layer of insulator over all MOS transistor and EEPROM cell locations and etching to form vias through said insulation layer where source and drain contacts are to be formed, said deposition being accomplished by PECVD or some other process which will form an insulator of high enough quality and at a temperature below the glass transition temperature of said substrate using chemicals and/or gases which will not attack or otherwise damage said substrate;

depositing a layer of contact metallization conductor such as metal or silicides by physical vapor deposition (hereafter PVD), chemical vapor deposition (hereafter CVD), PECVD, evaporation or sputtering or some other suitable process and photolithographically etching to form lead line

conductors to make all necessary source and drain connections from each MOS transistor or EEPROM cell to other devices needed to establish at least part of the connections needed for the functionality of the integrated circuit being formed, said deposition being accomplished at a temperature below the glass transition temperature of said substrate;

depositing a layer of amorphous silicon which is between 10 and 5000 nanometers thick by sputtering or by plasma enhanced chemical vapor deposition hereafter referred to as PECVD using processing steps performed at temperatures or in a manner which will not exceed the glass transition temperature of said substrate and using chemicals and/or gases which will not chemically attack or otherwise damage said substrate;

if higher mobilities or higher ON currents or lower threshold voltages for MOS transistors are needed for the transistors to be formed in said silicon layer than can be achieved in amorphous silicon, crystallizing said silicon layer to polycrystalline or microcrystalline form by pulse annealing the silicon layer with an excimer laser having a 308 nm wavelength using pulse durations of 30 nanoseconds or less full width at half maximum and energy density between 30-600 mJ/cm² per pulse using one or more pulses;

masking off areas of said integrated circuit where EEPROM cells, if any, are to be formed, and depositing a layer of gate insulator by PECVD at a temperature below the glass transition temperature of said substrate, said layer having a thickness suitable for thin film metal-oxide-semiconductor transistor device operation, typically between 20-500 nanometers thick;

masking off areas where MOS transistors are being formed to expose areas where EEPROM memory cells are to be formed and depositing one or more layers of gate insulator to form an insulation layer that is to lie below the floating gate, the thickness and materials selected for said one or more layers of gate insulator being such as to achieve Fowler-Noordheim tunnelling to the floating gate from a channel region at whatever programming voltage can be achieved on said integrated circuit, said

76 deposition being accomplished by PECVD at a temperature below the glass
77 transition temperature of said substrate;

78 depositing a layer of gate conductor, typically metal or silicides by
79 physical vapor deposition (hereafter PVD), chemical vapor deposition
80 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
81 process to form a control gate at the MOS transistor locations and a floating
82 gate at the EEPROM cell locations, said deposition being accomplished at a
83 temperature below the glass transition temperature of said substrate;

84 masking off locations where MOS transistors are being formed to leave
85 exposed only locations where EEPROM cells are being formed, and depositing a
86 layer of intergate insulator from which will be formed the insulation layer
87 between the floating gate and the control gate of each EEPROM cell, said
88 deposition being accomplished by PECVD or some other process which will
89 form an insulator of high enough quality to prevent charge leakage from said
90 floating gate and at a temperature below the glass transition temperature of
91 said substrate;

92 masking off locations where MOS transistors are being formed to leave
93 exposed only locations where EEPROM cells are being formed, and depositing a
94 layer of metal or silicide from which the control gate of all EEPROM cells is
95 to be formed, said deposition being by PVD, CVD, PECVD, evaporation or
96 sputtering or some other suitable process and accomplished at a temperature
97 below the glass transition temperature of said substrate;

98 performing the necessary photolithographic etching to define the gate
99 islands at both said MOS transistor and EEPROM cell locations, said
100 photolithographic etching being accomplished at temperatures below the glass
101 transition temperature of said substrate and using chemicals and/or gases
102 which will not attach or otherwise damage said substrate;

103 doping the source and drain regions of all said MOS transistors and
104 EEPROM cells using the Gas Immersion Laser Doping process or any other
105 suitable doping process which can dope said source and drain regions to
106 suitable conductivity and which crystallizes said amorphous silicon by pulsed

laser annealing and which can be accomplished at a temperature below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

photolithographically etching to define the lateral extents of each thin film transistor island at each MOS transistor and EEPROM cell, said photolithographic etching being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

depositing an insulation layer over all MOS transistors and EEPROM cells and etching vias therethrough for control gate contacts at all MOS transistor and EEPROM cell locations, said deposition being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

depositing a layer of contact metallization conductor to fill said via holes and cover each MOS transistors and EEPROM cell location and the spaces therebetween, and photolithographically etching the conductor layer to form a contact metallization to connect all the control gates of all MOS transistors and EEPROM cells to other nodes in the circuit to form the rest of the connections necessary to form a desired integrated circuit functionality.

11. A process for manufacturing an integrated circuit with MOS and ROM cells formed over an antenna on a substrate comprising:
- selecting a plastic or plastic laminated to glass substrate having a large size which is compatible with the substrate size capacity of flat panel display manufacturing machines to be used to do the subsequent deposition, photolithography, etching and laser crystallization and annealing steps necessary to form said integrated circuit thereon;
 - using flat panel display manufacturing machines to perform the following steps:

10 depositing a layer of insulating material which has a thickness and
11 Young's Modulus which are selected in light of the thickness and Young's
12 Modulus of said substrate so as to reduce differential strain at anticipated
13 operating temperatures so as to eliminate or reduce reliability problems
14 using processing steps performed at temperatures or in a manner which will
15 not exceed the glass transition temperature of said substrate and using
16 chemicals which will not chemically attack or otherwise damage said
17 substrate;

18
19 forming an antenna with one or more terminals on said layer of insulating
20 material deposited in the previous step at a plurality of locations on said substrate
21 by any prior art process such as silk screening or deposition and photolithographic
22 etching accomplished at temperatures below the glass transition temperature of said
23 substrate and using chemicals and/or gases that will not attack or otherwise damage
24 said substrate;

25
26 using flat panel display manufacturing machines to perform the following steps:

27 depositing a layer of pad contact conductor such as metal or silicides
28 by physical vapor deposition (hereafter PVD), chemical vapor deposition
29 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
30 process and photolithographically etching to form lead line conductors from
31 each antenna terminal to the locations where RF input/output terminals of
32 each corresponding integrated circuit will be formed, said deposition being
33 accomplished at a temperature below the glass transition temperature of said
34 substrate;

35 depositing a layer of insulator over all MOS transistor and ROM cell
36 locations and etching to form vias through said insulation layer where source
37 and drain contacts are to be formed, said deposition being accomplished by
38 PECVD or some other process which will form an insulator of high enough
39 quality and at a temperature below the glass transition temperature of said

40 substrate using chemicals and/or gases which will not attack or otherwise
41 damage said substrate;

42 depositing a layer of contact metallization conductor such as metal or
43 silicides by physical vapor deposition (hereafter PVD), chemical vapor
44 deposition (hereafter CVD), PECVD, evaporation or sputtering or some other
45 suitable process and photolithographically etching to form lead line
46 conductors to make all necessary source and drain connections from each MOS
47 transistor or ROM cell to other devices needed to establish at least part of the
48 connections needed for the functionality of the integrated circuit being
49 formed, said deposition being accomplished at a temperature below the glass
50 transition temperature of said substrate;

51 depositing a layer of amorphous silicon which is between 10 and
52 5000 nanometers thick by sputtering or by plasma enhanced chemical vapor
53 deposition hereafter referred to as PECVD using processing steps performed
54 at temperatures or in a manner which will not exceed the glass transition
55 temperature of said substrate and using chemicals and/or gases which will
56 not chemically attack or otherwise damage said substrate;

57 if higher mobilities or higher ON currents or lower threshold
58 voltages for MOS transistors are needed for the transistors to be formed in
59 said silicon layer than can be achieved in amorphous silicon, crystallizing said
60 silicon layer to polycrystalline or microcrystalline form by pulse annealing
61 the silicon layer with an excimer laser having a 308 nm wavelength using
62 pulse durations of 30 nanoseconds or less full width at half maximum and
63 energy density between 30-600 mJ/cm² per pulse using one or more pulses;

64 masking off areas of said integrated circuit where ROM cells, if any,
65 are to be formed, and depositing a layer of gate insulator by PECVD at a
66 temperature below the glass transition temperature of said substrate, said
67 layer having a thickness suitable for thin film metal-oxide-semiconductor
68 transistor device operation, typically between 20-500 nanometers thick;

69 masking off areas where MOS transistors are being formed to expose
70 areas where ROM memory cells are to be formed and depositing one or more

71 layers of gate insulator to form an insulation layer that is to lie below the
72 floating gate, the thickness and materials selected for said one or more layers
73 of gate insulator being such as to achieve Fowler-Noordheim tunnelling to the
74 floating gate from a channel region at whatever programming voltage can be
75 achieved on said integrated circuit, said deposition being accomplished by
76 PECVD at a temperature below the glass transition temperature of said
77 substrate;

78 depositing a layer of gate conductor, typically metal or silicides by
79 physical vapor deposition (hereafter PVD), chemical vapor deposition
80 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
81 process to form a control gate at the MOS transistor locations and a floating
82 gate at the ROM cell locations, said deposition being accomplished at a
83 temperature below the glass transition temperature of said substrate;

84 masking off locations where MOS transistors are being formed to leave
85 exposed only locations where ROM cells are being formed, and depositing a
86 layer of intergate insulator from which will be formed the insulation layer
87 between the floating gate and the control gate of each ROM cell, said deposition
88 being accomplished by PECVD or some other process which will form an
89 insulator of high enough quality to prevent charge leakage from said floating
90 gate and at a temperature below the glass transition temperature of said
91 substrate;

92 masking off locations where MOS transistors are being formed to leave
93 exposed only locations where ROM cells are being formed, and depositing a
94 layer of metal or silicide from which the control gate of all ROM cells is to be
95 formed, said deposition being by PVD, CVD, PECVD, evaporation or sputtering
96 or some other suitable process and accomplished at a temperature below the
97 glass transition temperature of said substrate;

98 performing the necessary photolithographic etching to define the gate
99 islands at both said MOS transistor and ROM cell locations, said
100 photolithographic etching being accomplished at temperatures below the glass

transition temperature of said substrate and using chemicals and/or gases which will not attach or otherwise damage said substrate;

doping the source and drain regions of all said MOS transistors and ROM cells using the Gas Immersion Laser Doping process or any other suitable doping process which can dope said source and drain regions to suitable conductivity and which crystallizes said amorphous silicon by pulsed laser annealing and which can be accomplished at a temperature below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

photolithographically etching to define the lateral extents of each thin film transistor island at each MOS transistor and ROM cell, said photolithographic etching being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attach or otherwise damage said substrate;

depositing an insulation layer over all MOS transistors and ROM cells and etching vias therethrough for control gate contacts at all MOS transistor and ROM cell locations, said deposition being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

depositing a layer of contact metallization conductor to fill said via holes and cover each MOS transistors and ROM cell location and the spaces therebetween, and photolithographically etching the conductor layer to form a contact metallization to connect all the control gates of all MOS transistors and ROM cells to other nodes in the circuit to form the rest of the connections necessary to form a desired integrated circuit functionality.

12. A process of making a large number of integrated EEPROM or ROM or static RAM cells on a large substrate comprising:

selecting a glass substrate having a large size which is compatible with the substrate size capacity of flat panel display manufacturing machines to be used to do

196 the subsequent deposition, photolithography, etching and laser crystallization and
 197 annealing steps necessary to form said EEPROM or ROM or static RAM cells thereon;
 198 using flat panel display manufacturing machines to do the insulation, metal
 199 and semiconductor deposition steps, and the photolithography, etching and pulsed
 200 laser crystallization and annealing steps necessary to form a plurality of EEPROM or
 201 ROM or static RAM memory cells directly on said glass substrate, all said processing
 202 steps performed at temperatures or in a manner which will not exceed the glass
 203 transition temperature of said substrate and using chemicals which will not
 204 chemically attack or otherwise damage said substrate.

1 13. A process for manufacturing an integrated circuit including MOS transistors and
 2 EEPROM cells on a substrate comprising:

3 selecting a glass substrate having a large size which is compatible with the
 4 substrate size capacity of flat panel display manufacturing machines to be used to do
 5 the subsequent deposition, photolithography, etching and laser crystallization and
 6 annealing steps necessary to form said integrated circuit thereon;

7 using flat panel display manufacturing machines to perform the following
 8 steps:

9 depositing a layer of insulating material using processing steps
 10 performed at temperatures or in a manner which will not exceed the glass
 11 transition temperature of said substrate and using chemicals which will not
 12 chemically attack or otherwise damage said substrate;

13 depositing a layer of amorphous silicon which is between 10 and
 14 5000 nanometers thick by sputtering or by plasma enhanced chemical vapor
 15 deposition hereafter referred to as PECVD using processing steps performed
 16 at temperatures or in a manner which will not exceed the glass transition
 17 temperature of said substrate and using chemicals and/or gases which will
 18 not chemically attack or otherwise damage said substrate;

19 if higher mobilities or higher ON currents or lower threshold
 20 voltages for MOS transistors are needed for the transistors to be formed in
 21 said silicon layer than can be achieved in amorphous silicon, crystallizing said

silicon layer to polycrystalline or microcrystalline form by pulse annealing the silicon layer with an excimer laser having a 308 nm wavelength using pulse durations of 30 nanoseconds or less full width at half maximum and energy density between 30-600 mJ/cm² per pulse using one or more pulses;

masking off areas of said integrated circuit where EEPROM cells, if any, are to be formed, and depositing a layer of gate insulator by PECVD at a temperature below the glass transition temperature of said substrate, said layer having a thickness suitable for thin film metal-oxide-semiconductor transistor device operation, typically between 20-500 nanometers thick;

masking off areas where MOS transistors are being formed to expose areas where EEPROM memory cells are to be formed and depositing one or more layers of gate insulator to form an insulation layer that is to lie below the floating gate, the thickness and materials selected for said one or more layers of gate insulator being such as to achieve Fowler-Noordheim tunnelling to the floating gate from a channel region at whatever programming voltage can be achieved on said integrated circuit, said deposition being accomplished by PECVD at a temperature below the glass transition temperature of said substrate;

depositing a layer of gate conductor, typically metal or silicides by physical vapor deposition (hereafter PVD), chemical vapor deposition (hereafter CVD), PECVD, evaporation or sputtering or some other suitable process to form a control gate at the MOS transistor locations and a floating gate at the EEPROM cell locations, said deposition being accomplished at a temperature below the glass transition temperature of said substrate;

masking off locations where MOS transistors are being formed to leave exposed only locations where EEPROM cells are being formed, and depositing a layer of intergate insulator from which will be formed the insulation layer between the floating gate and the control gate of each EEPROM cell, said deposition being accomplished by PECVD or some other process which will form an insulator of high enough quality to prevent charge leakage from said

52 floating gate and at a temperature below the glass transition temperature of
53 said substrate;

54 masking off locations where MOS transistors are being formed to leave
55 exposed only locations where EEPROM cells are being formed, and depositing a
56 layer of metal or silicide from which the control gate of all EEPROM cells is
57 to be formed, said deposition being by PVD, CVD, PECVD, evaporation or
58 sputtering or some other suitable process and accomplished at a temperature
59 below the glass transition temperature of said substrate;

60 performing the necessary photolithographic etching to define the gate
61 islands at both said MOS transistor and EEPROM cell locations, said
62 photolithographic etching being accomplished at temperatures below the glass
63 transition temperature of said substrate and using chemicals and/or gases
64 which will not attach or otherwise damage said substrate;

65 doping the source and drain regions of all said MOS transistors and
66 EEPROM cells using the Gas Immersion Laser Doping process or any other
67 suitable doping process which can dope said source and drain regions to
68 suitable conductivity and which crystallizes said amorphous silicon by pulsed
69 laser annealing and which can be accomplished at a temperature below the
70 glass transition temperature of said substrate and using chemicals and/or
71 gases which will not attack or otherwise damage said substrate;

72 photolithographically etching to define the lateral extents of each thin
73 film transistor island at each MOS transistor and EEPROM cell, said
74 photolithographic etching being accomplished at temperatures below the glass
75 transition temperature of said substrate and using chemicals and/or gases
76 which will not attach or otherwise damage said substrate;

77 depositing an insulation layer over all MOS transistors and EEPROM
78 cells and etching vias therethrough for source, drain and control gate contacts
79 at all MOS transistor and EEPROM cell locations, said deposition being
80 accomplished at temperatures below the glass transition temperature of said
81 substrate and using chemicals and/or gases which will not attack or
82 otherwise damage said substrate;

83 depositing a layer of contact metallization conductor to fill said via
84 holes and cover each MOS transistors and EEPROM cell location and the spaces
85 therebetween, and photolithographically etching the conductor layer to form a
86 contact metallization to connect all the MOS transistors and EEPROM cells
87 together to form the desired integrated circuit functionality.

1 14. A process for manufacturing an integrated circuit including MOS transistors and
2 ROM cells on a substrate comprising:

3 selecting a glass substrate having a large size which is compatible with the
4 substrate size capacity of flat panel display manufacturing machines to be used to do
5 the subsequent deposition, photolithography, etching and laser crystallization and
6 annealing steps necessary to form said integrated circuit thereon;

7 using flat panel display manufacturing machines to perform the following
8 steps:

9 depositing a layer of insulating material using processing steps
10 performed at temperatures or in a manner which will not exceed the glass
11 transition temperature of said substrate and using chemicals which will not
12 chemically attack or otherwise damage said substrate;

13 depositing a layer of amorphous silicon which is between 10 and 500
14 nanometers thick by sputtering or by plasma enhanced chemical vapor
15 deposition hereafter referred to as PECVD using processing steps performed
16 at temperatures or in a manner which will not exceed the glass transition
17 temperature of said substrate and using chemicals and/or gases which will
18 not chemically attack or otherwise damage said substrate;

19 if higher mobilities or higher ON currents or lower threshold
20 voltages for MOS transistors are needed for the transistors to be formed in
21 said silicon layer than can be achieved in amorphous silicon, crystallizing said
22 silicon layer to polycrystalline or microcrystalline form by pulse annealing
23 the silicon layer with an excimer laser having a 308 nm wavelength using
24 pulse durations of 30 nanoseconds or less full width at half maximum and
25 energy density between 30-600 mJ/cm² per pulse using one or more pulses;

masking off areas of said integrated circuit where ROM cells, if any, are to be formed, and depositing a layer of gate insulator by PECVD at a temperature below the glass transition temperature of said substrate, said layer having a thickness suitable for thin film metal-oxide-semiconductor transistor device operation, typically between 20-500 nanometers thick;

masking off areas where MOS transistors are being formed to expose areas where ROM memory cells are to be formed and depositing one or more layers of gate insulator to form an insulation layer that is to lie below the floating gate, the thickness and materials selected for said one or more layers of gate insulator being such as to achieve Fowler-Noordheim tunnelling to the floating gate from a channel region at whatever programming voltage can be achieved on said integrated circuit, said deposition being accomplished by PECVD at a temperature below the glass transition temperature of said substrate;

depositing a layer of gate conductor, typically metal or silicides by physical vapor deposition (hereafter PVD), chemical vapor deposition (hereafter CVD), PECVD, evaporation or sputtering or some other suitable process to form a control gate at the MOS transistor locations and a floating gate at the ROM cell locations, said deposition being accomplished at a temperature below the glass transition temperature of said substrate;

masking off locations where MOS transistors are being formed to leave exposed only locations where ROM cells are being formed, and depositing a layer of intergate insulator from which will be formed the insulation layer between the floating gate and the control gate of each ROM cell, said deposition being accomplished by PECVD or some other process which will form an insulator of high enough quality to prevent charge leakage from said floating gate and at a temperature below the glass transition temperature of said substrate;

masking off locations where MOS transistors are being formed to leave exposed only locations where ROM cells are being formed, and depositing a layer of metal or silicide from which the control gate of all ROM cells is to be

57 formed, said deposition being by PVD, CVD, PECVD, evaporation or sputtering
58 or some other suitable process and accomplished at a temperature below the
59 glass transition temperature of said substrate;

60 performing the necessary photolithographic etching to define the gate
61 islands at both said MOS transistor and ROM cell locations, said
62 photolithographic etching being accomplished at temperatures below the glass
63 transition temperature of said substrate and using chemicals and/or gases
64 which will not attack or otherwise damage said substrate;

65 doping the source and drain regions of all said MOS transistors and
66 ROM cells using the Gas Immersion Laser Doping process or any other
67 suitable doping process which can dope said source and drain regions to
68 suitable conductivity and which crystallizes said amorphous silicon by pulsed
69 laser annealing and which can be accomplished at a temperature below the
70 glass transition temperature of said substrate and using chemicals and/or
71 gases which will not attack or otherwise damage said substrate;

72 photolithographically etching to define the lateral extents of each thin
73 film transistor island at each MOS transistor and ROM cell, said
74 photolithographic etching being accomplished at temperatures below the glass
75 transition temperature of said substrate and using chemicals and/or gases
76 which will not attack or otherwise damage said substrate;

77 depositing an insulation layer over all MOS transistors and ROM cells
78 and etching vias therethrough for source, drain and control gate contacts at
79 all MOS transistor and ROM cell locations, said deposition being accomplished
80 at temperatures below the glass transition temperature of said substrate and
81 using chemicals and/or gases which will not attack or otherwise damage said
82 substrate;

83 depositing a layer of contact metallization conductor to fill said via
84 holes and cover each MOS transistors and ROM cell location and the spaces
85 therebetween, and photolithographically etching the conductor layer to form a
86 contact metallization to connect all the MOS transistors and ROM cells
87 together to form the desired integrated circuit functionality.

1 15. A process for manufacturing an integrated circuit with MOS and EEPROM cells
2 formed over an antenna on a substrate comprising:

3 selecting a glass substrate having a large size which is compatible with the
4 substrate size capacity of flat panel/display manufacturing machines to be used to do
5 the subsequent deposition, photolithography, etching and laser crystallization and
6 annealing steps necessary to form said integrated circuit thereon;

7 using flat panel display manufacturing machines to perform the following
8 steps:

9 depositing a layer of insulating material using processing steps
10 performed at temperatures or in a manner which will not exceed the glass
11 transition temperature of said substrate and using chemicals which will not
12 chemically attack or otherwise damage said substrate;

13
14 forming an antenna with one or more terminals on said layer of insulating
15 material deposited in the previous step at a plurality of locations on said substrate
16 by any prior art process such as silk screening or deposition and photolithographic
17 etching accomplished at temperatures below the glass transition temperature of said
18 substrate and using chemicals and/or gases that will not attack or otherwise damage
19 said substrate;

20
21 using flat panel display manufacturing machines to perform the following steps:

22 depositing a layer of pad contact conductor such as metal or silicides
23 by physical vapor deposition (hereafter PVD), chemical vapor deposition
24 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
25 process and photolithographically etching to form lead line conductors from
26 each antenna terminal to the locations where RF input/output terminals of
27 each corresponding integrated circuit will be formed, said deposition being
28 accomplished at a temperature below the glass transition temperature of said
29 substrate;

30 depositing a layer of insulator over all MOS transistor and EEPROM
31 cell locations and etching to form vias through said insulation layer where
32 source and drain contacts are to be formed, said deposition being accomplished
33 by PECVD or some other process which will form an insulator of high enough
34 quality and at a temperature below the glass transition temperature of said
35 substrate using chemicals and/or gases which will not attack or otherwise
36 damage said substrate;

37 depositing a layer of contact metallization conductor such as metal or
38 silicides by physical vapor deposition (hereafter PVD), chemical vapor
39 deposition (hereafter CVD), PECVD, evaporation or sputtering or some other
40 suitable process and photolithographically etching to form lead line
41 conductors to make all necessary source and drain connections from each MOS
42 transistor or EEPROM cell to other devices needed to establish at least part of
43 the connections needed for the functionality of the integrated circuit being
44 formed, said deposition being accomplished at a temperature below the glass
45 transition temperature of said substrate;

46 depositing a layer of amorphous silicon which is between 10 and
47 5000 nanometers thick by sputtering or by plasma enhanced chemical vapor
48 deposition hereafter referred to as PECVD using processing steps performed
49 at temperatures or in a manner which will not exceed the glass transition
50 temperature of said substrate and using chemicals and/or gases which will
51 not chemically attack or otherwise damage said substrate;

52 if higher mobilities or higher ON currents or lower threshold
53 voltages for MOS transistors are needed for the transistors to be formed in
54 said silicon layer than can be achieved in amorphous silicon, crystallizing said
55 silicon layer to polycrystalline or microcrystalline form by pulse annealing
56 the silicon layer with an excimer laser having a 308 nm wavelength using
57 pulse durations of 30 nanoseconds or less full width at half maximum and
58 energy density between 30-600 mJ/cm² per pulse using one or more pulses;

59 masking off areas of said integrated circuit where EEPROM cells, if
60 any, are to be formed, and depositing a layer of gate insulator by PECVD at a

61 temperature below the glass transition temperature of said substrate, said
62 layer having a thickness suitable for thin film metal-oxide-semiconductor
63 transistor device operation, typically between 20-500 nanometers thick;

64 masking off areas where MOS transistors are being formed to expose
65 areas where EEPROM memory cells are to be formed and depositing one or
66 more layers of gate insulator to form an insulation layer that is to lie below
67 the floating gate, the thickness and materials selected for said one or more
68 layers of gate insulator being such as to achieve Fowler-Noordheim
69 tunnelling to the floating gate from a channel region at whatever
70 programming voltage can be achieved on said integrated circuit, said
71 deposition being accomplished by PECVD at a temperature below the glass
72 transition temperature of said substrate;

73 depositing a layer of gate conductor, typically metal or silicides by
74 physical vapor deposition (hereafter PVD), chemical vapor deposition
75 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
76 process to form a control gate at the MOS transistor locations and a floating
77 gate at the EEPROM cell locations, said deposition being accomplished at a
78 temperature below the glass transition temperature of said substrate;

79 masking off locations where MOS transistors are being formed to leave
80 exposed only locations where EEPROM cells are being formed, and depositing a
81 layer of intergate insulator from which will be formed the insulation layer
82 between the floating gate and the control gate of each EEPROM cell, said
83 deposition being accomplished by PECVD or some other process which will
84 form an insulator of high enough quality to prevent charge leakage from said
85 floating gate and at a temperature below the glass transition temperature of
86 said substrate;

87 masking off locations where MOS transistors are being formed to leave
88 exposed only locations where EEPROM cells are being formed, and depositing a
89 layer of metal or silicide from which the control gate of all EEPROM cells is
90 to be formed, said deposition being by PVD, CVD, PECVD, evaporation or

91 sputtering or some other suitable process and accomplished at a temperature
92 below the glass transition temperature of said substrate;
93 performing the necessary photolithographic etching to define the gate
94 islands at both said MOS transistor and EEPROM cell locations, said
95 photolithographic etching being accomplished at temperatures below the glass
96 transition temperature of said substrate and using chemicals and/or gases
97 which will not attach or otherwise damage said substrate;
98 doping the source and drain regions of all said MOS transistors and
99 EEPROM cells using the Gas Immersion Laser Doping process or any other
100 suitable doping process which can dope said source and drain regions to
101 suitable conductivity and which crystallizes said amorphous silicon by pulsed
102 laser annealing and which can be accomplished at a temperature below the
103 glass transition temperature of said substrate and using chemicals and/or
104 gases which will not attack or otherwise damage said substrate;
105 photolithographically etching to define the lateral extents of each thin
106 film transistor island at each MOS transistor and EEPROM cell, said
107 photolithographic etching being accomplished at temperatures below the glass
108 transition temperature of said substrate and using chemicals and/or gases
109 which will not attach or otherwise damage said substrate;
110 depositing an insulation layer over all MOS transistors and EEPROM
111 cells and etching vias therethrough for control gate contacts at all MOS
112 transistor and EEPROM cell locations, said deposition being accomplished at
113 temperatures below the glass transition temperature of said substrate and
114 using chemicals and/or gases which will not attack or otherwise damage said
115 substrate;
116 depositing a layer of contact metallization conductor to fill said via
117 holes and cover each MOS transistors and EEPROM cell location and the spaces
118 therebetween, and photolithographically etching the conductor layer to form a
119 contact metallization to connect all the control gates of all MOS transistors
120 and EEPROM cells to other nodes in the circuit to form the rest of the
121 connections necessary to form a desired integrated circuit functionality.

1 16. A process for manufacturing an integrated circuit with MOS and ROM cells
2 formed over an antenna on a substrate comprising:

3 selecting a glass substrate having a large size which is compatible with the
4 substrate size capacity of flat panel display manufacturing machines to be used to do
5 the subsequent deposition, photolithography, etching and laser crystallization and
6 annealing steps necessary to form said integrated circuit thereon;

7 using flat panel display manufacturing machines to perform the following
8 steps:

9 depositing a layer of insulating material which has a thickness and
10 Young's Modulus which are selected in light of the thickness and Young's
11 Modulus of said substrate so as to reduce differential strain at anticipated
12 operating temperatures so as to eliminate or reduce reliability problems
13 using processing steps performed at temperatures or in a manner which will
14 not exceed the glass transition temperature of said substrate and using
15 chemicals which will not chemically attack or otherwise damage said
16 substrate;

17
18 forming an antenna with one or more terminals on said layer of insulating
19 material deposited in the previous step at a plurality of locations on said substrate
20 by any prior art process such as silk screening or deposition and photolithographic
21 etching accomplished at temperatures below the glass transition temperature of said
22 substrate and using chemicals and/or gases that will not attack or otherwise damage
23 said substrate;

24
25 using flat panel display manufacturing machines to perform the following steps:

26 depositing a layer of pad contact conductor such as metal or silicides
27 by physical vapor deposition (hereafter PVD), chemical vapor deposition
28 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
29 process and photolithographically etching to form lead line conductors from
30 each antenna terminal to the locations where RF input/output terminals of

31 each corresponding integrated circuit will be formed, said deposition being
32 accomplished at a temperature below the glass transition temperature of said
33 substrate;

34 depositing a layer of insulator over all MOS transistor and ROM cell
35 locations and etching to form vias through said insulation layer where source
36 and drain contacts are to be formed, said deposition being accomplished by
37 PECVD or some other process which will form an insulator of high enough
38 quality and at a temperature below the glass transition temperature of said
39 substrate using chemicals and/or gases which will not attack or otherwise
40 damage said substrate;

41 depositing a layer of contact metallization conductor such as metal or
42 silicides by physical vapor deposition (hereafter PVD), chemical vapor
43 deposition (hereafter CVD), PECVD, evaporation or sputtering or some other
44 suitable process and photolithographically etching to form lead line
45 conductors to make all necessary source and drain connections from each MOS
46 transistor or ROM cell to other devices needed to establish at least part of the
47 connections needed for the functionality of the integrated circuit being
48 formed, said deposition being accomplished at a temperature below the glass
49 transition temperature of said substrate;

50 depositing a layer of amorphous silicon which is between 10 and
51 5000 nanometers thick by sputtering or by plasma enhanced chemical vapor
52 deposition hereafter referred to as PECVD using processing steps performed
53 at temperatures or in a manner which will not exceed the glass transition
54 temperature of said substrate and using chemicals and/or gases which will
55 not chemically attack or otherwise damage said substrate;

56 if higher mobilities or higher ON currents or lower threshold
57 voltages for MOS transistors are needed for the transistors to be formed in
58 said silicon layer than can be achieved in amorphous silicon, crystallizing said
59 silicon layer to polycrystalline or microcrystalline form by pulse annealing
60 the silicon layer with an excimer laser having a 308 nm wavelength using

61 pulse durations of 30 nanoseconds or less full width at half maximum and
62 energy density between 30-600 mJ/cm² per pulse using one or more pulses;
63 masking off areas of said integrated circuit where ROM cells, if any,
64 are to be formed, and depositing a layer of gate insulator by PECVD at a
65 temperature below the glass transition temperature of said substrate, said
66 layer having a thickness suitable for thin film metal-oxide-semiconductor
67 transistor device operation, typically between 20-500 nanometers thick;
68 masking off areas where MOS transistors are being formed to expose
69 areas where ROM memory cells are to be formed and depositing one or more
70 layers of gate insulator to form an insulation layer that is to lie below the
71 floating gate, the thickness and materials selected for said one or more layers
72 of gate insulator being such as to achieve Fowler-Noordheim tunnelling to the
73 floating gate from a channel region at whatever programming voltage can be
74 achieved on said integrated circuit, said deposition being accomplished by
75 PECVD at a temperature below the glass transition temperature of said
76 substrate;
77 depositing a layer of gate conductor, typically metal or silicides by
78 physical vapor deposition (hereafter PVD), chemical vapor deposition
79 (hereafter CVD), PECVD, evaporation or sputtering or some other suitable
80 process to form a control gate at the MOS transistor locations and a floating
81 gate at the ROM cell locations, said deposition being accomplished at a
82 temperature below the glass transition temperature of said substrate;
83 masking off locations where MOS transistors are being formed to leave
84 exposed only locations where ROM cells are being formed, and depositing a
85 layer of intergate insulator from which will be formed the insulation layer
86 between the floating gate and the control gate of each ROM cell, said deposition
87 being accomplished by PECVD or some other process which will form an
88 insulator of high enough quality to prevent charge leakage from said floating
89 gate and at a temperature below the glass transition temperature of said
90 substrate;

masking off locations where MOS transistors are being formed to leave exposed only locations where ROM cells are being formed, and depositing a layer of metal or silicide from which the control gate of all ROM cells is to be formed, said deposition being by PVD, CVD, PECVD, evaporation or sputtering or some other suitable process and accomplished at a temperature below the glass transition temperature of said substrate;

performing the necessary photolithographic etching to define the gate islands at both said MOS transistor and ROM cell locations, said photolithographic etching being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

doping the source and drain regions of all said MOS transistors and ROM cells using the Gas Immersion Laser Doping process or any other suitable doping process which can dope said source and drain regions to suitable conductivity and which crystallizes said amorphous silicon by pulsed laser annealing and which can be accomplished at a temperature below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

photolithographically etching to define the lateral extents of each thin film transistor island at each MOS transistor and ROM cell, said photolithographic etching being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

depositing an insulation layer over all MOS transistors and ROM cells and etching vias therethrough for control gate contacts at all MOS transistor and ROM cell locations, said deposition being accomplished at temperatures below the glass transition temperature of said substrate and using chemicals and/or gases which will not attack or otherwise damage said substrate;

depositing a layer of contact metallization conductor to fill said via holes and cover each MOS transistors and ROM cell location and the spaces therebetween, and photolithographically etching the conductor layer to form a

122 contact metalization to connect all the control gates of all MOS transistors
123 and ROM cells to other nodes in the circuit to form the rest of the connections
124 necessary to form a desired integrated circuit functionality.
125
126

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